

NCE P-Channel Enhancement Mode Power MOSFET

Description

The NCE60P09S uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

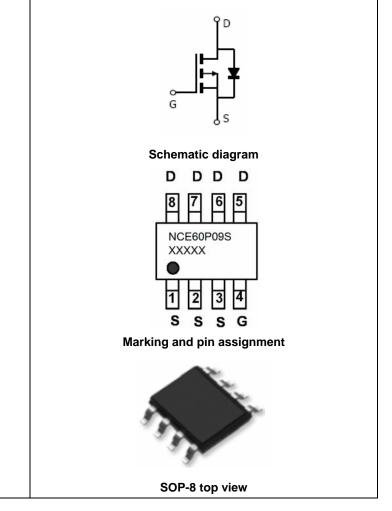
General Features

- V_{DS} =-60V,I_D =-9A
 R_{DS(ON)} <38mΩ @ V_{GS}=-10V
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE60P09S	NCE60P09S	SOP-8	-	-	-

Absolute Maximum Ratings (T_c=25[°]C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	-60	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	Ι _D	-9	А
Drain Current-Continuous(T _C =100℃)	I _D (100℃)	-6.4	A
Pulsed Drain Current	I _{DM}	36	A
Maximum Power Dissipation	PD	3.0	W
Single pulse avalanche energy (Note 5)	E _{AS}	156	mJ
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	R _{θJA}	41.7	°C/W]
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Electrical Characteristics (T_c=25[°]C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	····					
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250µA	-60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)	····					
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=-250\mu A$	-1.8	-2.6	-3.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-9A	-	32	38	mΩ
Forward Transconductance	g fs	V _{DS} =-5V,I _D =-9A	-	20	-	S
Dynamic Characteristics (Note4)	····					
Input Capacitance	C _{lss}		-	2049	-	PF
Output Capacitance	C _{oss}	V _{DS} =-30V,V _{GS} =0V, F=1.0MHz	-	112.7	-	PF
Reverse Transfer Capacitance	C _{rss}		-	88.7	-	PF
Switching Characteristics (Note 4)	····					
Turn-on Delay Time	t _{d(on)}		-	12	-	nS
Turn-on Rise Time	tr	V_{DD} =-30V,I _D =-9A	-	14	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =-10V,R _{GEN} =3Ω	-	38	-	nS
Turn-Off Fall Time	t _f		-	15	-	nS
Total Gate Charge	Qg	V _{DS} =-30V,I _D =-9A, V _{GS} =-10V	-	35.1	-	nC
Gate-Source Charge	Q _{gs}		-	9	-	nC
Gate-Drain Charge	Q _{gd}	V GS10 V	-	7.9	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-9A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	-9	А
Reverse Recovery Time	trr	TJ = 25°C, IF = -9A	-	-	40	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	-	70	nC

Notes:

 $\label{eq:constraint} \textbf{1.} \ \textbf{Repetitive Rating: Pulse width limited by maximum junction temperature.}$

2. Surface Mounted on FR4 Board, t \leq 10 sec.

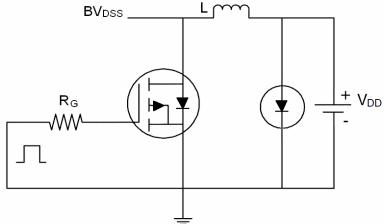
3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

4. Guaranteed by design, not subject to production

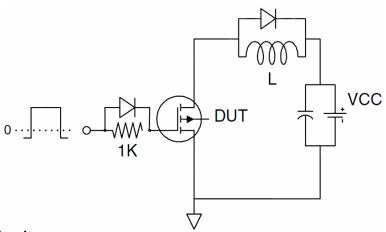
5. EAS condition: Tj=25 $^\circ\!\!\mathrm{C}$,V_DD=-30V,VG=-10V,L=0.5mH,Rg=25 Ω



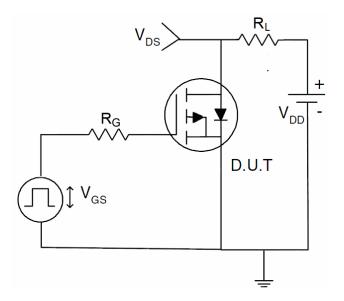
Test Circuit 1) E_{AS} Test Circuit



2) Gate Charge Test Circuit

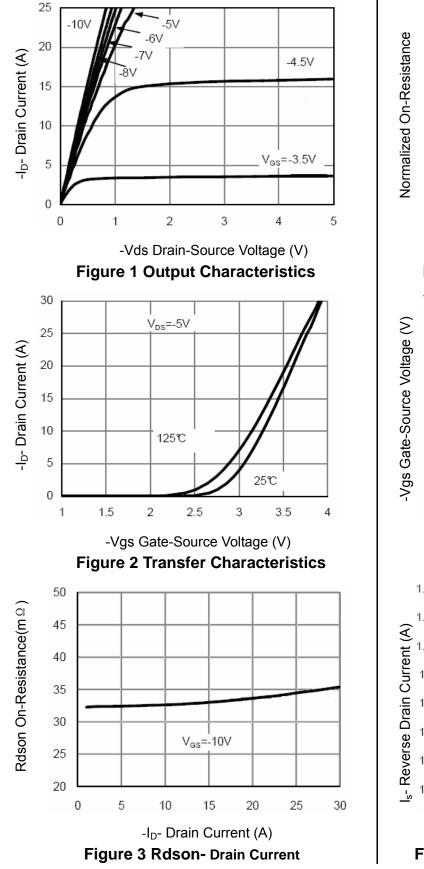


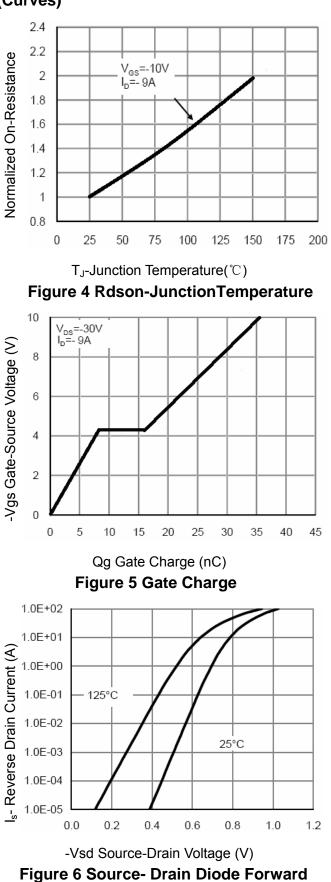
3) Switch Time Test Circuit





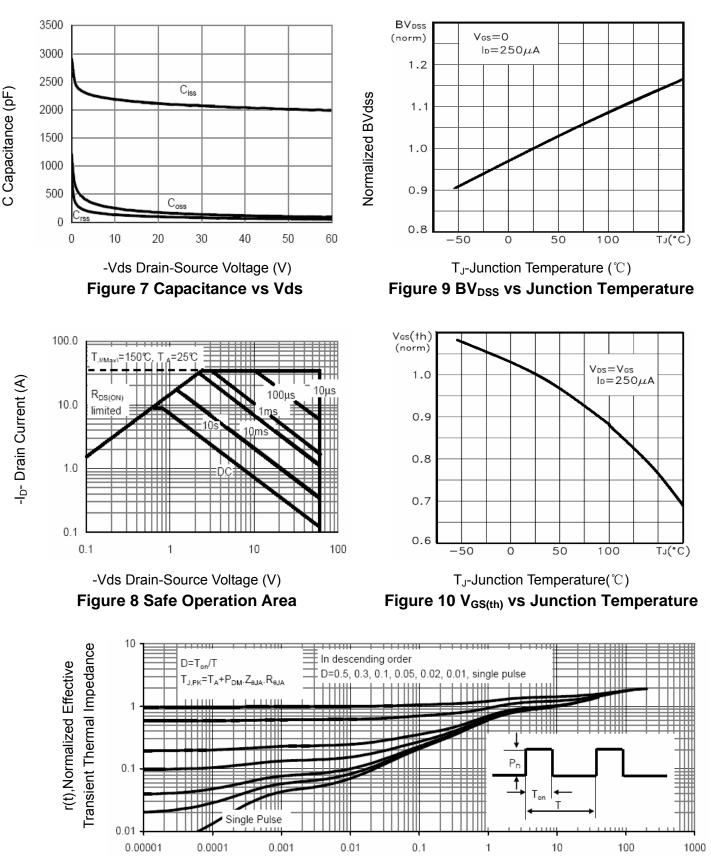
Typical Electrical and Thermal Characteristics (Curves)







http://www.ncepower.com



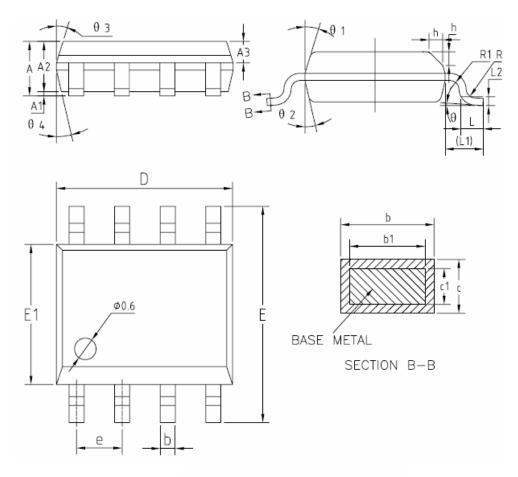
Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance

Wuxi NCE Power Co., Ltd



SOP-8 Package Information



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX	
Α	1.35	1.55	1.75	
A1	0.10	0.15	0.25	
A2	1.25	1.40	1.65	
A3	0.50	0.60	0.70	
b	0.38	-	0.51	
b1	0.37	0.42	0.47	
с	0.18	-	0.25	
c1	0.17	0.20	0.23	
D	4.80	4.90	5.00	
E	5.80	6.00	6.20	
E1	3.80	3.90	4.00	
e	1.17	1.27	1.37	
L	0.45	0.60	0.80	
L1		1.04REF		
L2	0.25BSC			
R	0.07	-	-	
R1	0.07	-	-	
h	0.30	0.40	0.50	
θ θ 1	0*	-	8*	
θ 1	15'	17	19'	
θ <u>2</u>	11.	13	15*	
θ3	15*	17	19*	
θ4	11*	13	15'	



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